

Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time

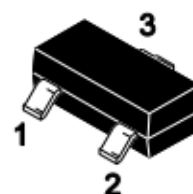
Equivalent Circuit

3.Cathode1、Cathode2



1.Anode1 2.Anode2

SOT-23



1.Anode1 2.Anode2
3.Cathode1、Cathode2

Marking Code : A61

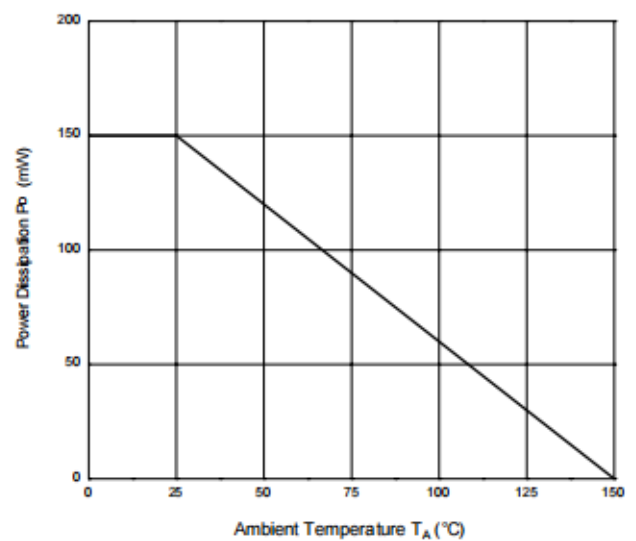
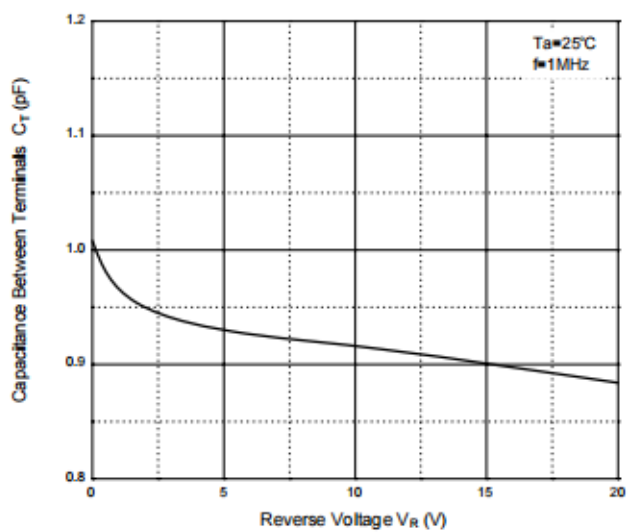
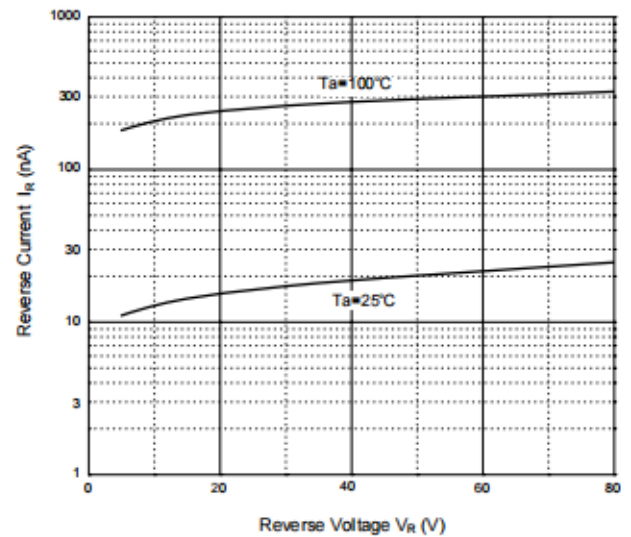
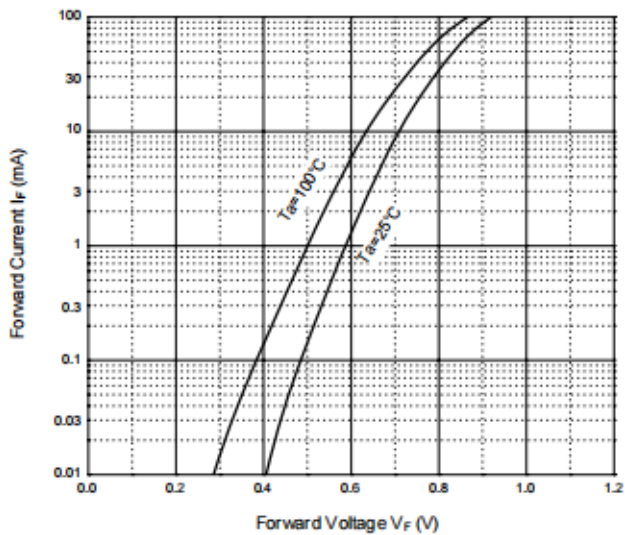
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	1	A
Maximum Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$)

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$	V_F	0.6 0.7 0.9	-- -- 1.2	V
Reverse Current at $V_R = 70\text{ V}$	I_R	--	1	μA
Typical Junction Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_j	--	4	pF
Maximum Reverse Recovery Time at $I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $I_{RR} = 0.1 \times I_R$, $R_L = 100\Omega$	T_{rr}	--	4	nS

Typical Characteristic Curves



Package Outline

SOT-23

Dimensions in mm

